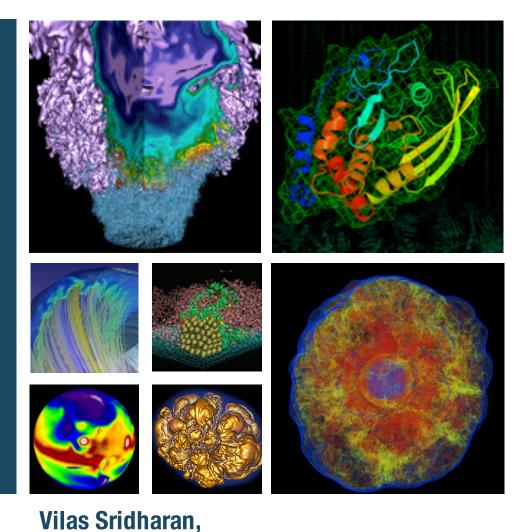
Memory Errors in Modern Systems The Good, The Bad, And The Ugly











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AMD WAS SUPPORTED BY DOE FAST FORWARD AND AMD RESEARCH



AMD

Collaborators

- Vilas Sridharan, AMD Research, Advanced Micro Devices Inc.
- Nathan Debardeleben, Ultrascale Systems Research Center, Los Alamos National Laboratory
- Sean Blanchard, Ultrascale Systems Research Center, Los Alamos National Laboratory
- Sudhanva Gurumurthi, AMD Research, Advanced Micro Devices Inc.
- Jon Stearley, Scalable Architectures, Sandia National Laboratories
- Kurt B. Ferreira, Scalable Architectures, Sandia National Laboratories
- John Shalf, NERSC and CRD, Lawrence Berkeley National Laboratory

Thanks to

- AMD Inc. who were central to the study
- Many folks at Cray Inc. for dumping error logs
- NERSC Systems staff, including Tina Butler and Jay Srinivasan



















- Reliability is crucial for large-scale systems
- Must confirm reliability models are accurate
- Use data from real systems to correlate to models

Cielo at Los Alamos National Lab



8-core AMD Opteron™ CPUs

8,944 nodes: 1,144,832 DRAM

DDR-3 DRAM, Chipkill-correct ECC

Hopper at NERSC / Lawrence Berkeley National Lab



12-core AMD Opteron™ CPUs

6,384 nodes: 817,152 DRAM

DDR-3 DRAM, Chipkill-detect ECC

Production systems
500M+ CPU socket-hours
40B+ DRAM device-hours





Sources of Failure



- Solder joints and other connector/mechanical failures
- Ephemeral bit upset is tied to energetic particle strikes

(probability is proportional to surface area exposure)



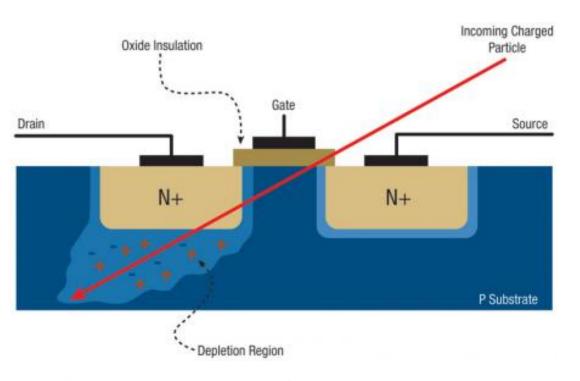


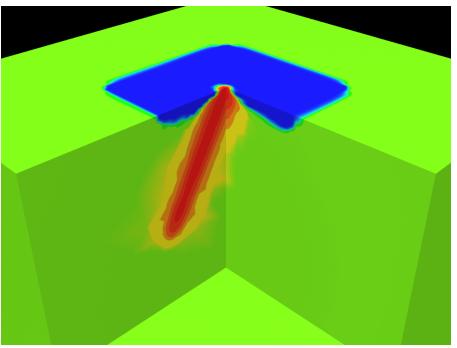




Why Focus on Memory

- HPC has an overwhelming obsession with compute
- But most of your computer is in fact memory
- And the probability of a bit upset is proportional to silicon surface area



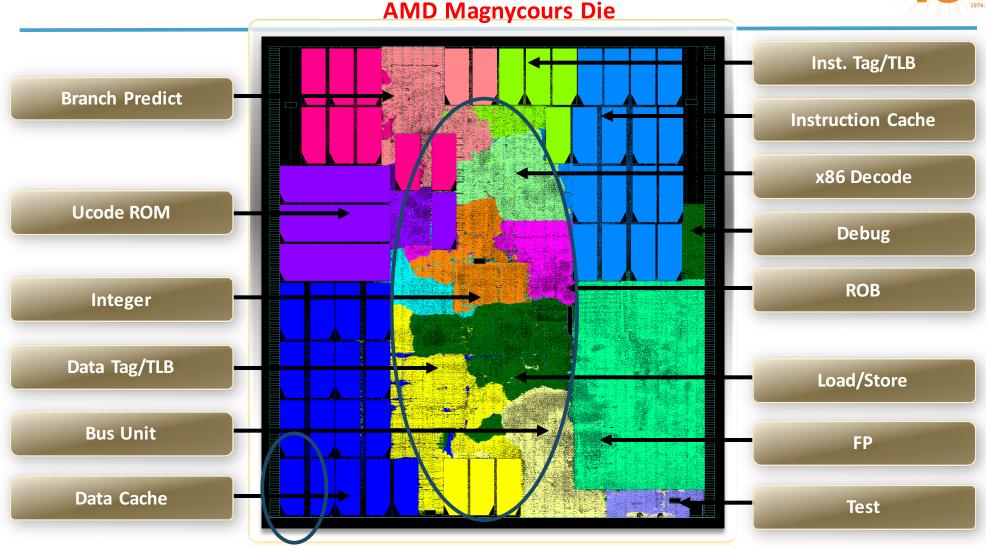






SRAM Structures Consume a LOT of Area on Modern CPUs Nersc





Each rectangle contains 16k bits of SRAM

100k+ flip flops and latches





DRAM Involves a lot of Discrete Components and even MORE Silicon Surface Area



Dynamic random-access memory (DRAM)

- Used for almost all computer main memory
- Single-capacitor memory
- Reads are destructive must rewrite data after read ("precharge")
- Capacitors lose charge over time must periodically rewrite data ("refresh")



- Laptop: O(1-10 GB) of DRAM
- Petascale supercomputer: O(10-100 TB) of DRAM

DRAM reliability will be critical in the future

- Exascale: O(1-100 PB) of DRAM
- In-package (die-stacked) DRAM











Motivation



Architectural & micro-architectural approaches to reliability

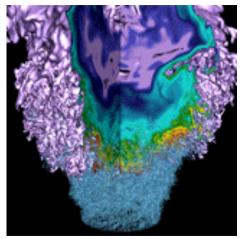
To get it right, you must know the faults to expect

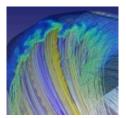
 This talk looks at faults collected in production systems in the field (validating the fault model)



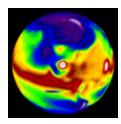


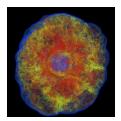
Terminology and Methodology

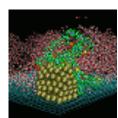


















Failure Rates in Context What is a FIT?



A FIT is ONE failure per Billion hours of operation

- A FIT rate of 1 corresponds to....
 - 1 Billion hours of operation Failure every 115,000 years
 - For 8,944 nodes (Cielo): Failure every 12.8 years
 - For 71,552 DIMMs: Failure every 1.6 years
 - For 1,144,832 DRAM chips: Failure every 36 days
- Real FIT rates (FIT rates for components on Cielo)
 - Target socket FIT rate of 1000: failure every 2.3 days
 - Target DRAM chip FIT rate of 35: failure every 1 days





Terminology



Fault

 The underlying cause of an error, such as a stuck-at bit or high-energy particle strike

Transient fault

- Return incorrect data until overwritten
- Random and not indicative of device damage

Hard fault

- Consistently return an incorrect value
- Repair by disabling or by replacing the faulty device

Intermittent fault

- Sometimes return an incorrect value
- Under specific conditions such as elevated temperature
- Indicative of device damage or malfunction

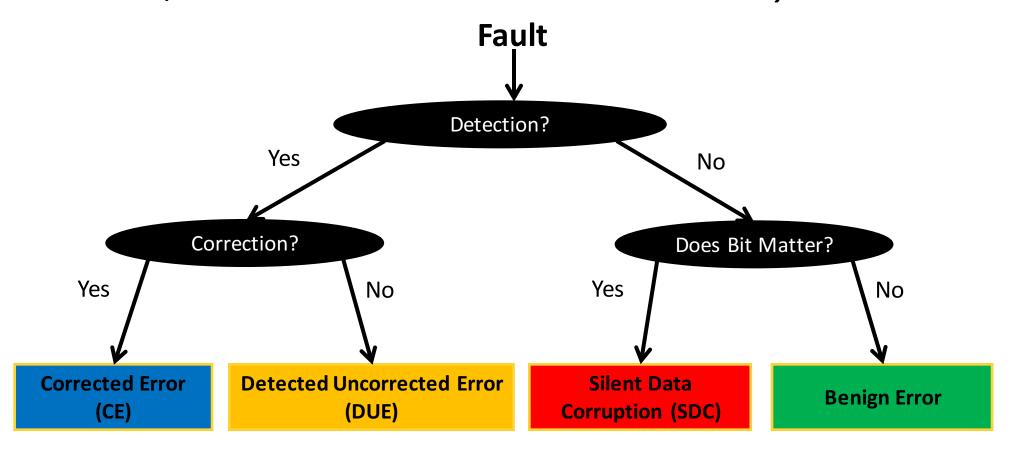
Permanent faults







 Error: An incorrect state resulting from an active Fault, such as an incorrect value in memory



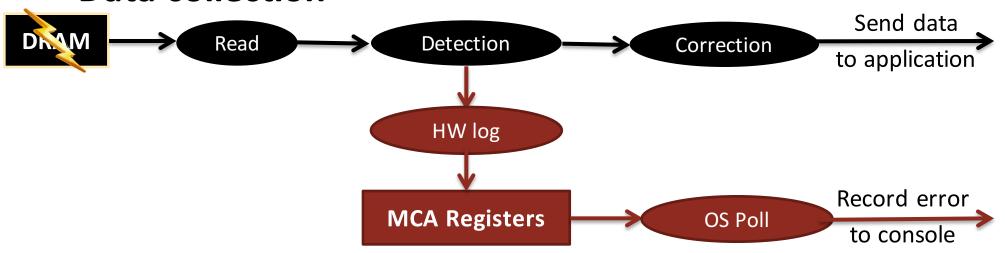




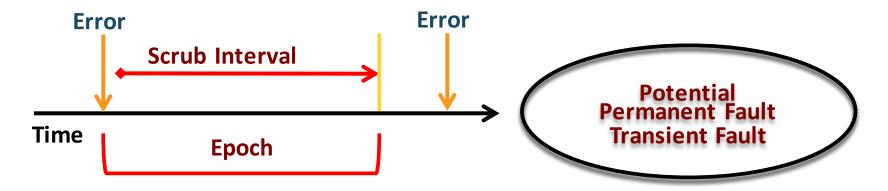
Methodology



Data collection



Use presence of scrubber to coalesce errors into faults

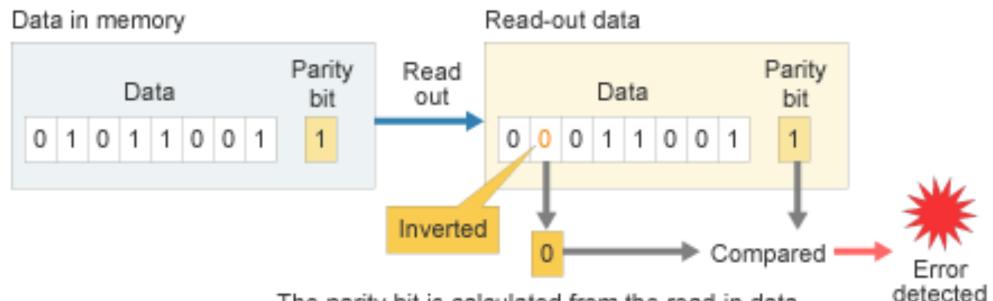






Parity Protection just detects errors





The parity bit is calculated from the read-in data. Since the number of 1s is an odd number, the parity bit is "0".

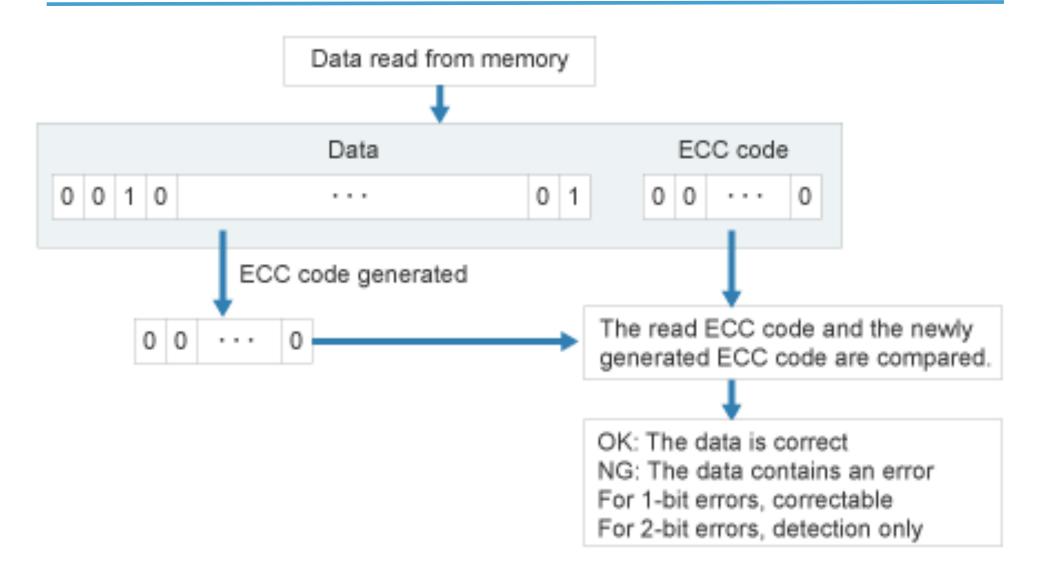




ECC (Error Correcting Code) Protection



(SEC-DED) Single Error Correct, Double Error Detect

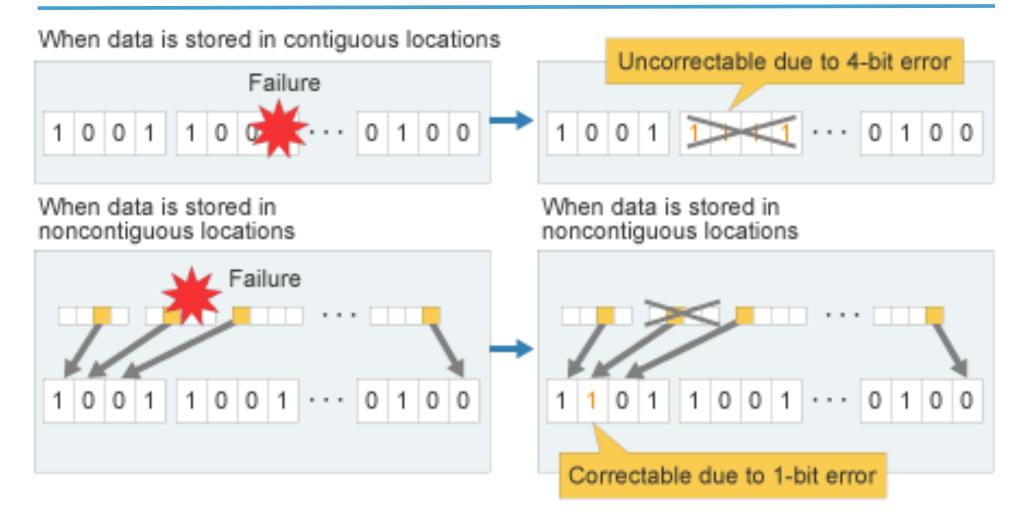








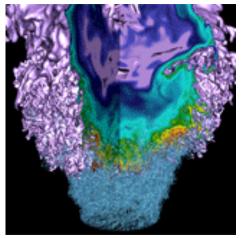
Interleaving Data for Protection (chip-kill)

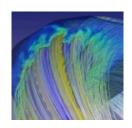




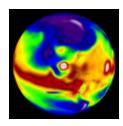


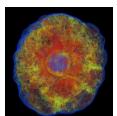
The Good

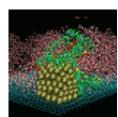


















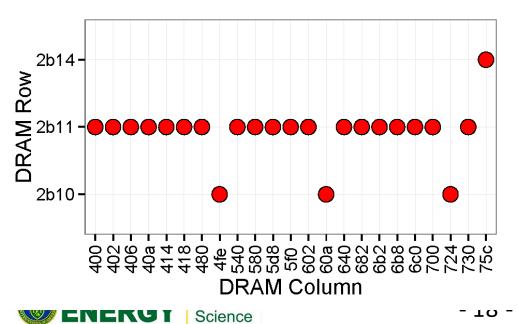
DRAM Fault Rates and MODES

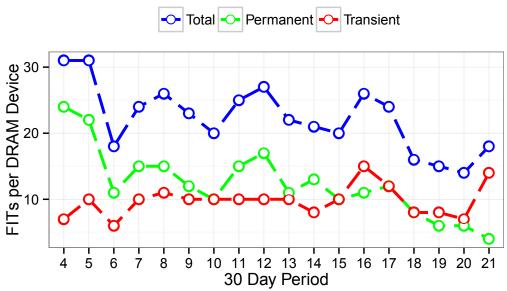
▲ Fault rates

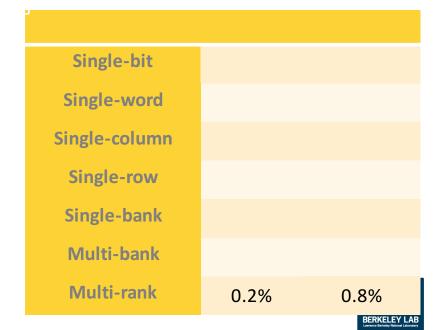
- Constant rate of transient faults
- Declining rate of permanent faults
- >50% permanent faults

▲ Fault modes

- Often affect multiple rows/columns



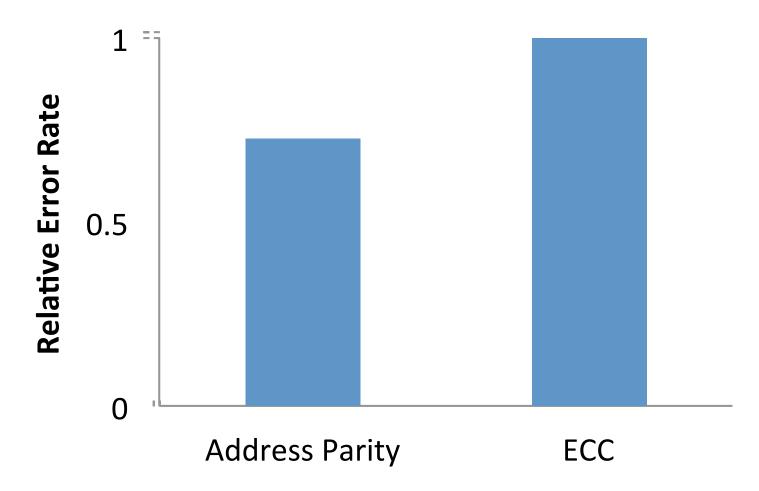








DDR-3 Address/command parity



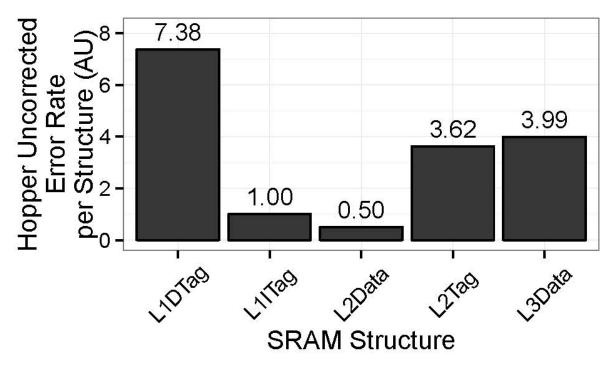
Address/command parity is a valuable addition to the DDR spec

U.S. DEPARTMENT OF Office of Science





SRAM: Case Study



- Uncorrected errors dominated by L1DTag
 - Small structure, ~50% of all errors
- L2Tag has ECC: why so many errors?
 - One bit per entry is covered by parity

Details matter: seemingly small decisions can have large impact on system reliability

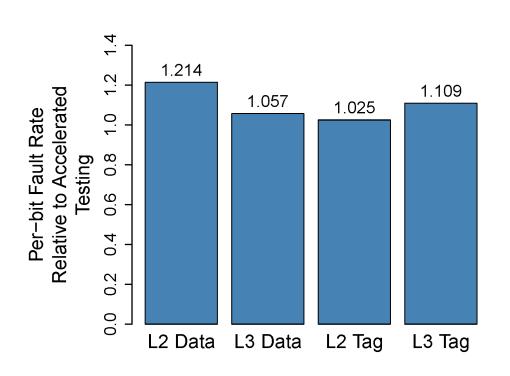


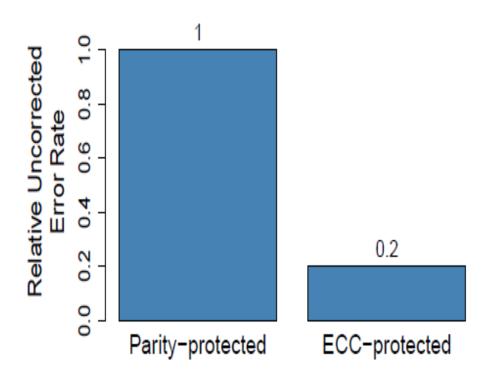
SRAM Faults

ACCELERATED TESTING CORRECTLY PREDICTS ERROR RATES IN THE FIELD

SRAM faults are well-understood

Most errors are from parity-protected structures





SRAM faults and mitigation techniques are well-understood



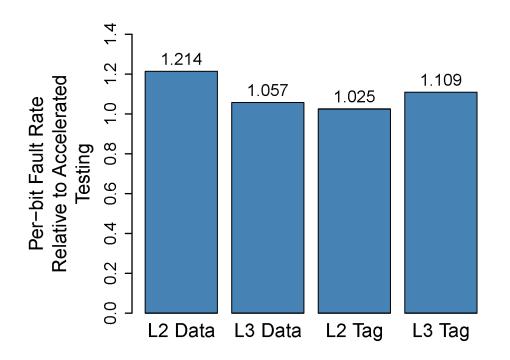


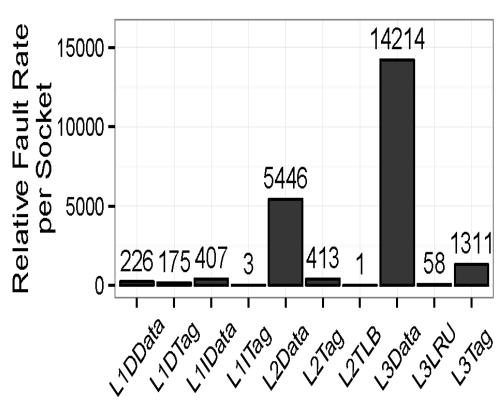
SRAM Faults

FAULT MODEL IS VALIDATED BY ACCELERATED TESTING AND FIELD DATA

SRAM faults are well-understood

At scale, even small structures see faults



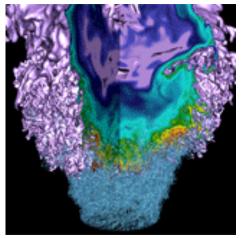


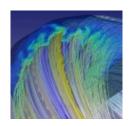
Chip architects must pay attention to reliable design (and they do)



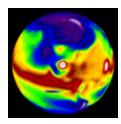


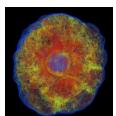
The Bad

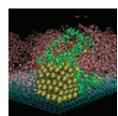














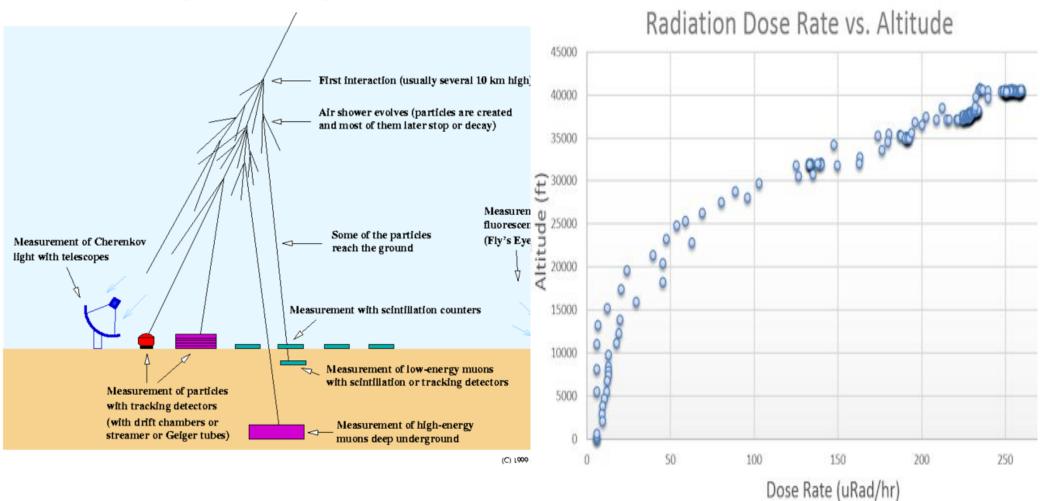




Altitude Effects



Measuring cosmic-ray and gamma-ray air showers

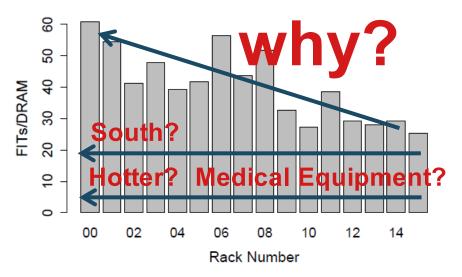


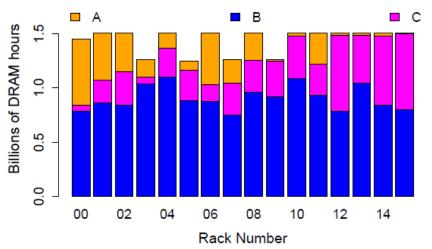




Location Dependence for DRAM Errors?

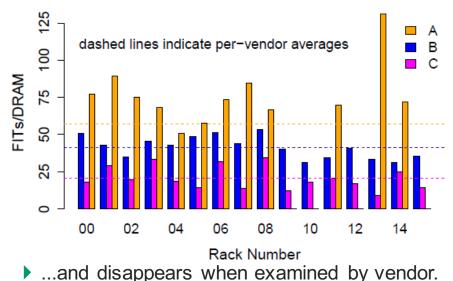






▶ A correlation to physical location...

...is due to non-uniform distribution of vendor...



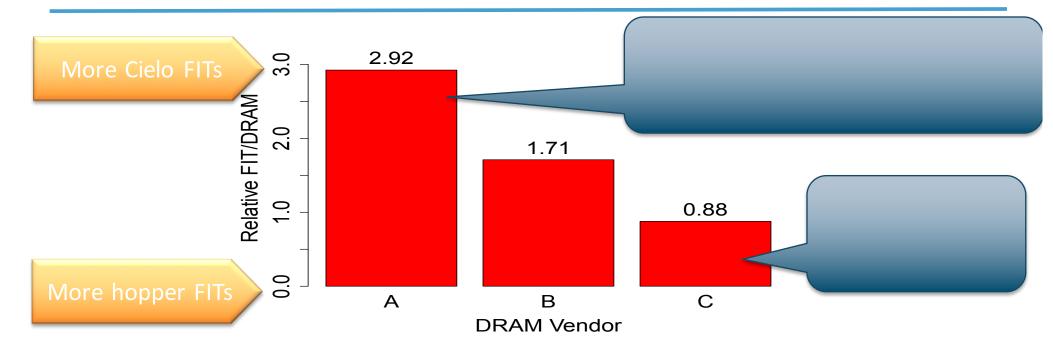
DRAM reliability studies must account for DRAM vendor or risk inaccurate conclusions







Altitude Effects in DRAM?



Difference in DRAM fault rate on Cielo vs. Hopper

Effect differs per vendor

Science

- Almost entirely due to a subset of fault modes (single-bit, single-column transient)
- Primary difference between the two systems is altitude
 - Cielo at 7000+ ft., Hopper at 43 ft.

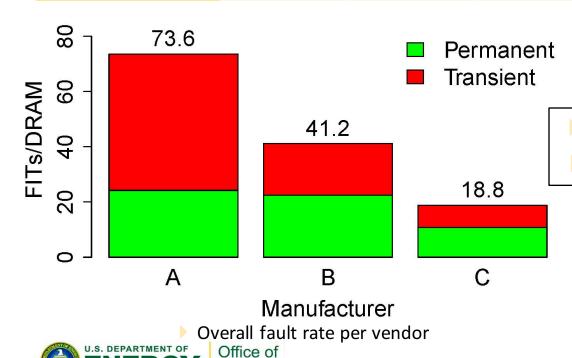




Vendor Effects



Fault Mode	Vendor A	Vendor B	Vendor C
Single-bit	64.6%	69.5%	58.4%
Single-word	0%	0.3%	0%
Single-column	8.7%	8.8%	11.9%
Single-row	12.2%	10.6%	14.9%
Single-bank	13.5%	7.8%	9.9%
Multiple-bank	1.3%	0.7%	2.0%
Multiple-rank	1.3%	3.0%	3.0%

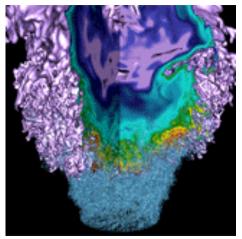


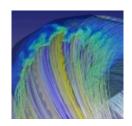
Science

- Fault modes are present across vendors
- Fault rates differ significantly by vendor

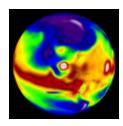


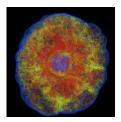
The Ugly

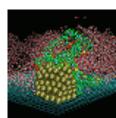
















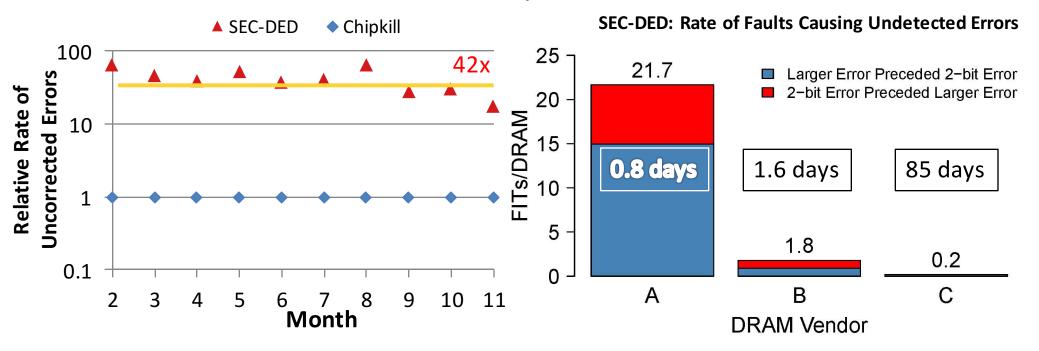




DRAM: Chipkill vs. SEC-DED ECC

Chipkill ECC

- The ability to correct any error from a single DRAM device
- Requires more overhead than SEC-DED ECC (12.5% instead of 7%)
- 30% multibit errors detectable by SEC-DED, but 70% were not



SEC-DED ECC is poorly suited to modern DRAM technology







Counting Faults vs. Counting Errors

- Counting logged errors overemphasizes the impact of permanent faults
 - Error events are not independent
 - A single fault generates an arbitrary number of errors (0 -> infinite)
 - Permanent faults tend to cause more errors than transient faults
- ▲ The logged corrected error count is meaningless for system health
 - Operating system polls for corrected errors (e.g., once every 10 seconds)
 - But a modern system can experience millions of errors per second
 - Console log contains a (small) sample of corrected errors
- ▲ The logged uncorrected error count is meaningful for system health
 - Every uncorrected error is reported to the operating system via interrupt
 - Console log contains an exact count of uncorrected errors

Incorrect methodology can lead to incorrect conclusions about system reliability

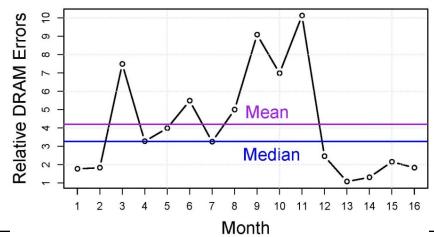




Hopper has a memory error rate 4x that of Cielo, but a memory fault rate 0.625x that of Cielo.

Error counts are confounded by other factors such as workload behavior, they are not an accurate measure of system health.

- Hopper's DRAM error rate was 4x greater than Cielo's ← Cielo is more reliable
- Reality: Hopper's DRAM fault rate was 37% lower than Cielo's

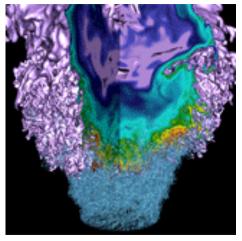


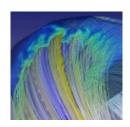
Incorrect methodology can lead to incorrect conclusions about system reliability



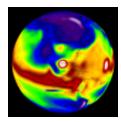


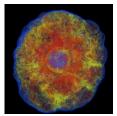
Projecting to Exascale

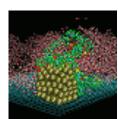












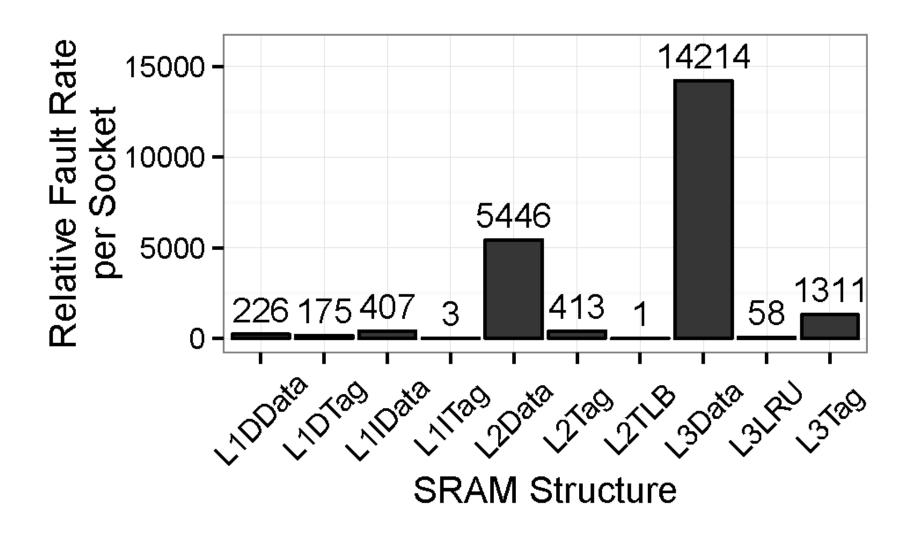


Science



SRAM: Projecting to Exascale

AT SCALE, EVEN SMALL STRUCTURES SEE FAULTS



Vendors must pay attention to reliable design





SRAM: Projecting to Exascale

SRAM UNCORRECTED ERROR RATE RELATIVE TO CIELO

▲ Two potential systems

- Small: 10k nodes

Large: 100k nodes

■ Same fault rate as 45nm

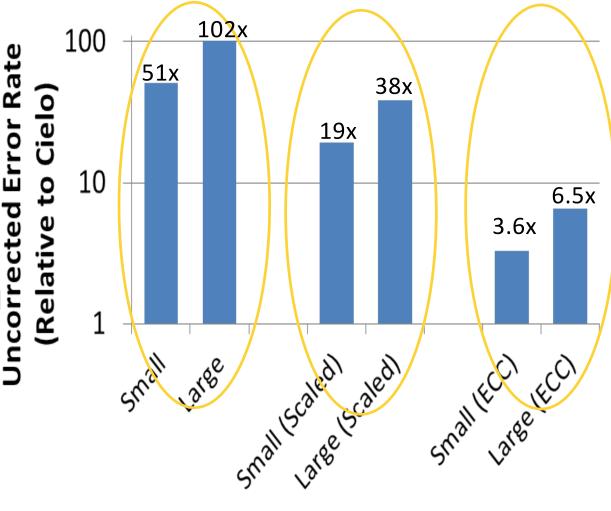
Sky is falling

Scale faults per current trend

- Sky falls more slowly
- Switch to FinFETs may make this even better

▲ Add some engineering effort

Sky stops falling

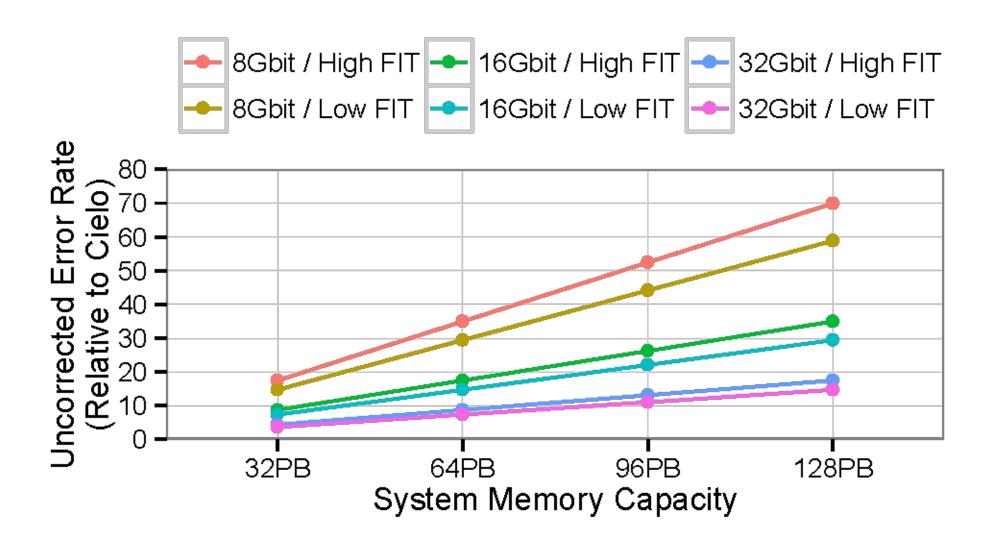


SRAM faults are unlikely to be a significantly larger problem than today





DRAM: Projecting to Exascale









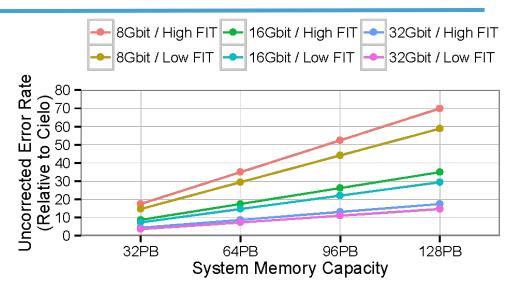


■ Uncorrected error rate

- 10-70x error rate of current systems
- Is the sky falling?

▲ This is not just a problem for exascale

- Cost problem for data centers / cloud
- Reliability problem in client (smart cars)?

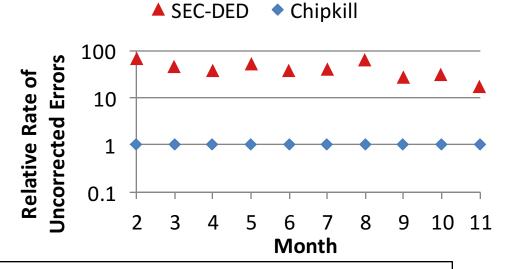


Solutions are out there

- Including for die-stacked DRAM?
- Lots of people working on this...

▲ Historical example

- Chipkill vs. SEC-DED



DRAM subsystems need higher reliability than today, but will likely get it



Conclusions



- Large systems require reliable design and reliability modeling
- Field data analysis is necessary to correlate reliability models and guide DOE investments
 - Must measure the underlying fault rate to correctly evaluate the model
 - Must track component supplier to make proper conclusions
- Collaboration between DOE researchers, vendors, and integrators, and facilities is critical to achieving this









SRAM Structures

- Likelihood of faults: very high
- Risk: low
- Why?: Model for particle strikes on CMOS SRAM remains solid (it's a matter of engineering and cost... no magic required)

JEDEC DIMM Structures

- Likelihood of faults: medium
- Risk: medium (lower if move to chip-kill)
- Why?: Component supplier has more pronounced effect than environmental factors. SEC-DED and DRAM is clearly insufficient

Stacked DRAM (HBM, etc...)

- Likelihood of faults: medium
- Risk: high (will be lower after field data collected from first sys.)
- Why?: No field test data to confirm very well thought-out models (might be no issue, but always risk for unverified model)

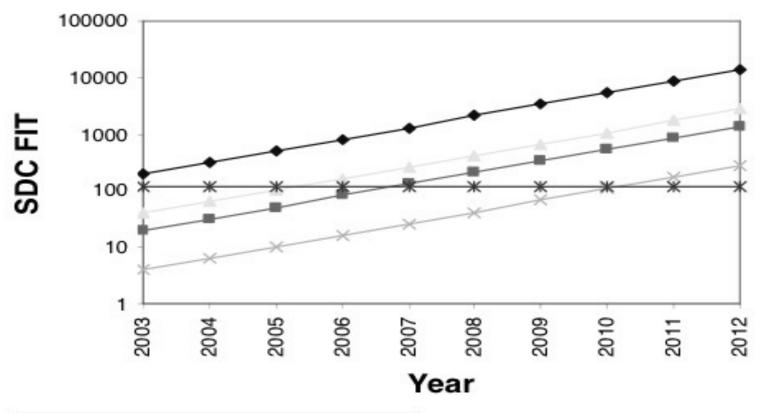


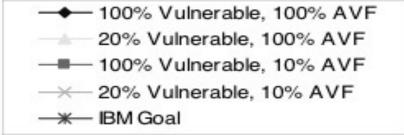


Reliability of Components Set by Market



(SER rates rising, but....)









Reliability of Components Set by Market

(set point for hardware resilience set by market) (be slighly more reliable than the OS)



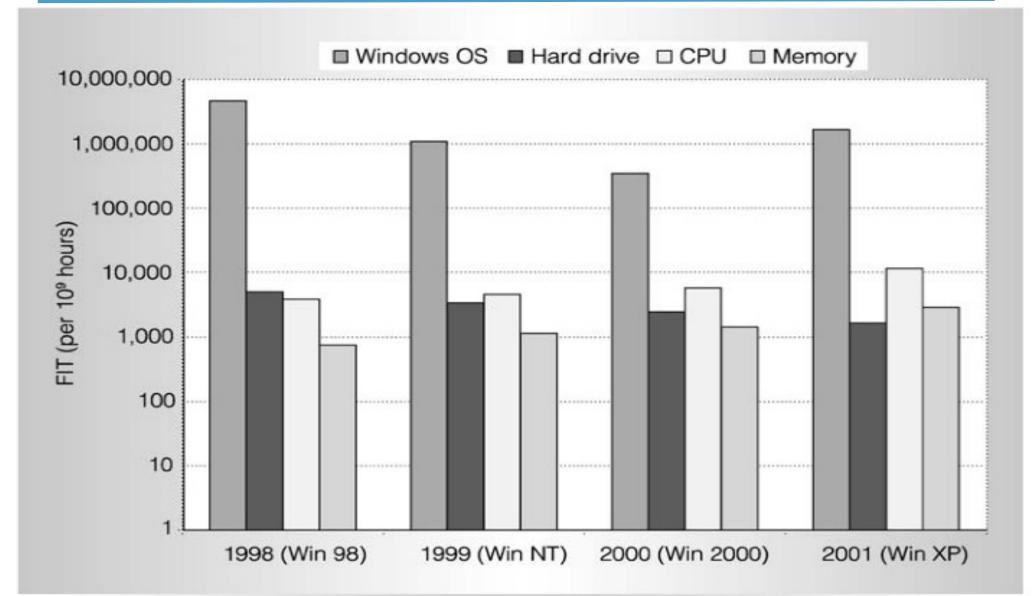


Figure 2. Failures in billions of hours of operation.2-5



Synergy with Embedded Industry

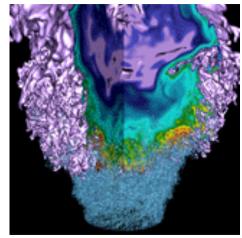
- The error tolerance requirements for self-driving vehicles are approaching that required
- The same microarchitecture error-tolerance techniques will be employed in both places (more leverage for HPC resilience)

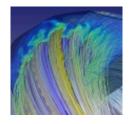
 ... I just wrote this a few seconds ago in response to Martin Berzins' question during the break... (so lets just talk about this)



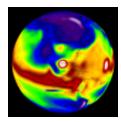


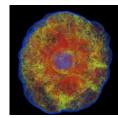
The End

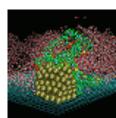


















References

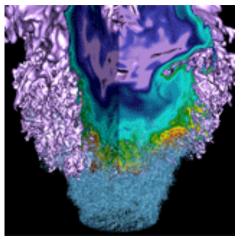


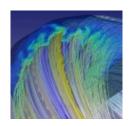
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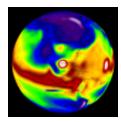


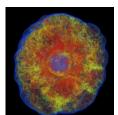
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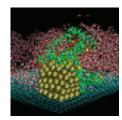












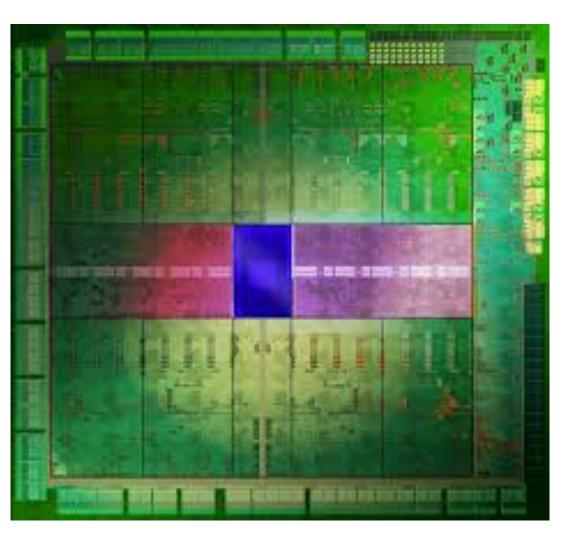






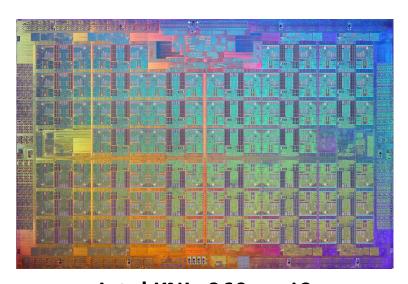
Die Sizes: Area affects probability of fault from energetic particles (e.g. cosmic rays)



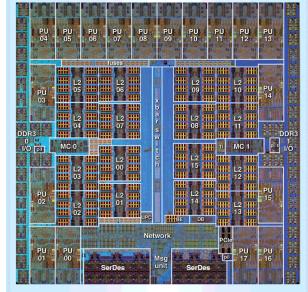


NVIDIA Maxwell: 600mm^2





Intel KNL: 360mm² (same area for **BG/Q chip**)







arXiv.org > astro-ph > arXiv:1410.2895

Astrophysics > Instrumentation and Methods for Astrophysics

Observing Ultra-High Energy Cosmic Rays with Smartphones

Daniel Whiteson, Michael Mulhearn, Chase Shimmin, Kyle Cranmer, Kyle Brodie, Dustin Burns

(Submitted on 10 Oct 2014 (v1), last revised 22 Oct 2015 (this version, v2))

We propose a novel approach for observing cosmic rays at ultra-high energy (> 10^{18} ~eV) by repurposing the existing network of smartphones as a ground detector array. Extensive air showers generated by cosmic rays produce muons and high-energy photons, which can be detected by the CMOS sensors of smartphone cameras. The small size and low efficiency of each sensor is compensated by the large number of active phones. We show that if user adoption targets are met, such a network will have significant observing power at the highest energies.

Comments: version 2

Subjects: Instrumentation and Methods for Astrophysics (astro-ph.IM); High Energy Astrophysical Phenomena (astro-ph.HE); High Energy Physics -

Phenomenology (hep-ph); Instrumentation and Detectors (physics.ins-det)

Cite as: arXiv:1410.2895 [astro-ph.IM]

(or arXiv:1410.2895v2 [astro-ph.IM] for this version)

Submission history

From: Daniel Whiteson [view email]

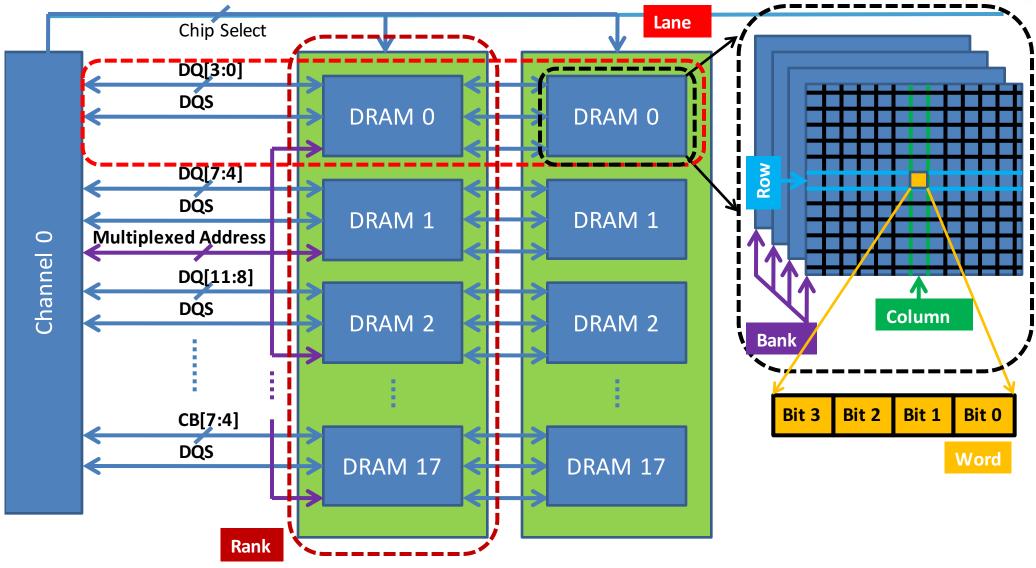
[v1] Fri, 10 Oct 2014 20:00:07 GMT (151kb,D)

[v2] Thu, 22 Oct 2015 20:25:31 GMT (619kb,D)

Which authors of this paper are endorsers? | Disable MathJax (What is MathJax?)

memory channel Organization







Each logical entity (e.g. row, rank) shares control logic

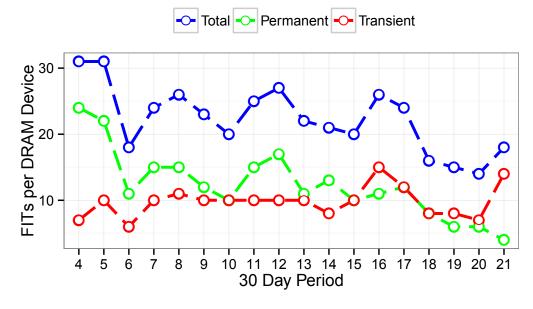
Office of Science



DRAM FAULT Rates and MODES

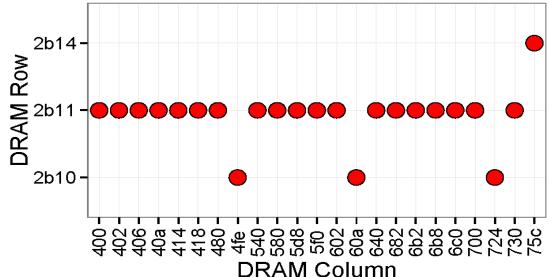
▲ Fault rates

- Constant rate of transient faults
- Declining rate of permanent faults
- >50% permanent faults



▲ Fault modes

- Often affect multiple rows/columns







The more more general techniques have more overhead (like TMR), but can be used for broad array of code without any understanding of the code. Mike Heroux's resilient elliptic solver is very specific to the mathematical formulation.



